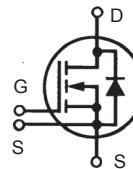


HiPerFET™ Power MOSFETs Single Die MOSFET

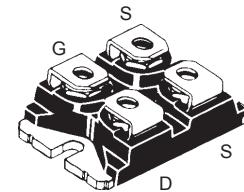
N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

IXFN 80N50



V_{DSS}	= 500	V
I_{D25}	= 80	A
$R_{DS(on)}$	= 55	$m\Omega$
t_{rr}	≤ 250	ns

miniBLOC, SOT-227 B (IXFN)
E153432



G = Gate D = Drain
S = Source

Either Source terminal of miniBLOC can be used as Main or Kelvin Source

Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ C$ to $150^\circ C$	500	V	
V_{DGR}	$T_J = 25^\circ C$ to $150^\circ C$; $R_{GS} = 1 M\Omega$	500	V	
V_{GS}	Continuous	± 20	V	
V_{GSM}	Transient	± 30	V	
I_{D25}	$T_c = 25^\circ C$, Chip capability	80	A	
I_{DM}	$T_c = 25^\circ C$, pulse width limited by T_{JM}	320	A	
I_{AR}	$T_c = 25^\circ C$	80	A	
E_{AR}	$T_c = 25^\circ C$	64	mJ	
E_{AS}	$T_c = 25^\circ C$	6	J	
dv/dt	$I_s \leq I_{DM}$, $dI/dt \leq 100 A/\mu s$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ C$, $R_G = 2 \Omega$	5	V/ns	
P_D	$T_c = 25^\circ C$	780	W	
T_J		-55 ... +150	$^\circ C$	
T_{JM}		150	$^\circ C$	
T_{stg}		-55 ... +150	$^\circ C$	
V_{ISOL}	50/60 Hz, RMS $t = 1$ min $I_{ISOL} \leq 1$ mA $t = 1$ s	2500 3000	V~ V~	
M_d	Mounting torque Terminal connection torque	1.5/13	Nm/lb.in. Nm/lb.in.	
Weight		30	g	

Symbol	Test Conditions	Characteristic Values		
		($T_J = 25^\circ C$, unless otherwise specified)	min.	typ.
V_{DSS}	$V_{GS} = 0 V$, $I_D = 3$ mA	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8$ mA	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 V_{DC}$, $V_{DS} = 0$			± 200 nA
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 V$	$T_J = 25^\circ C$ $T_J = 125^\circ C$		100 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10 V$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu s$, duty cycle $d \leq 2\%$			55 $m\Omega$

Applications

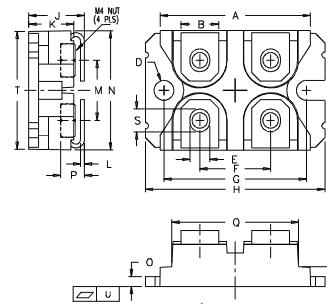
- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values			
		($T_J = 25^\circ\text{C}$, unless otherwise specified)	min.	typ.	max.
g_{fs}	$V_{DS} = 15 \text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	50	70	S	
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	9890	pF		
		1750	pF		
		460	pF		
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1 \Omega$ (External),	61	ns		
		70	ns		
		102	ns		
		27	ns		
$Q_{G(on)}$ Q_{GS} Q_{GD}	$V_{GS} = 10 \text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$	380	nC		
		80	nC		
		173	nC		
R_{thJC}			0.16	K/W	
R_{thCK}		0.05		K/W	

miniBLOC, SOT-227 B



M4 screws (4x) supplied

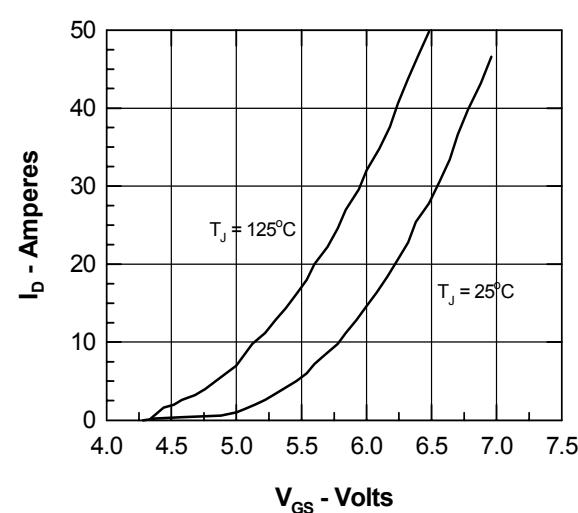
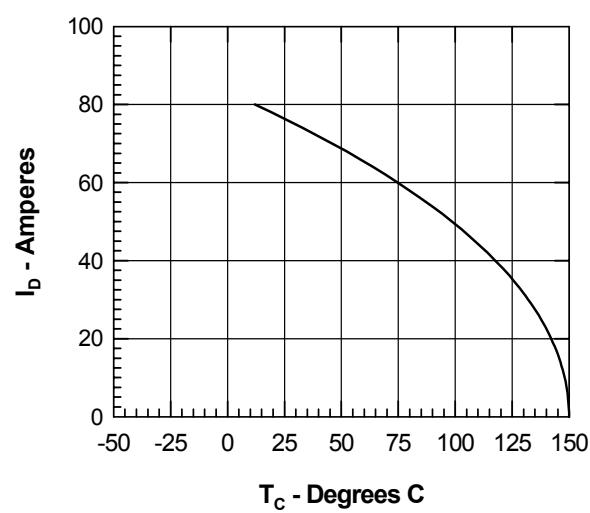
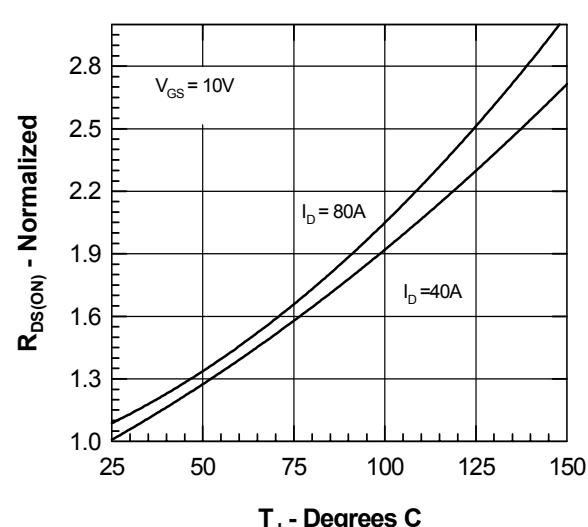
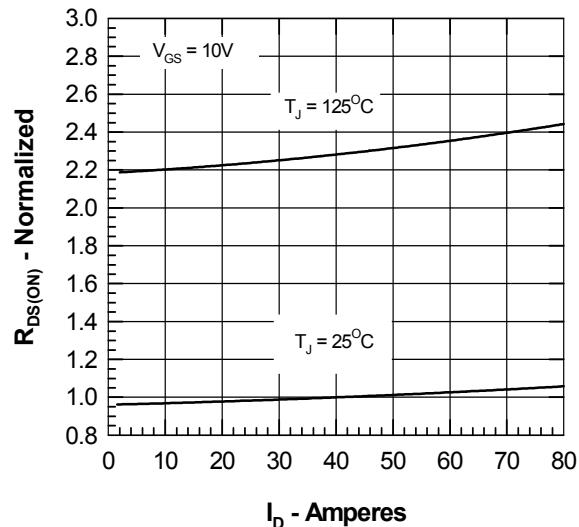
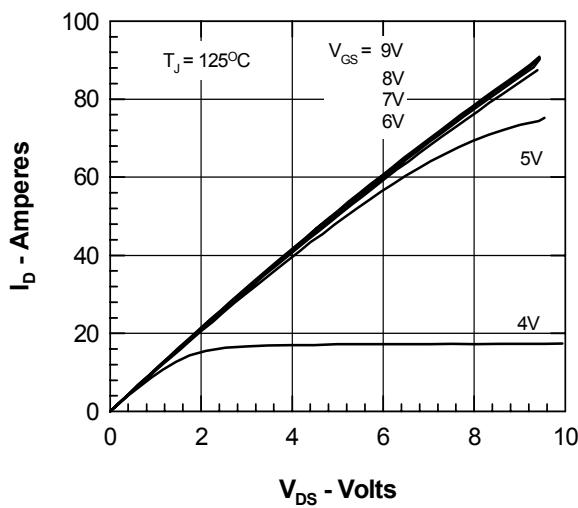
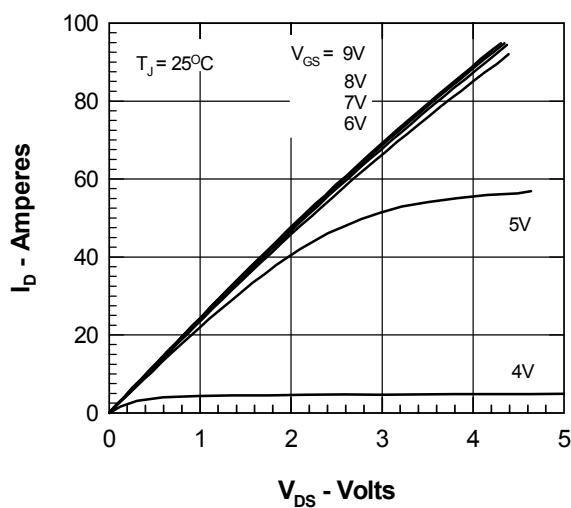
Dim.	Millimeter Min.	Millimeter Max.	Inches Min.	Inches Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

Source-Drain Diode

Characteristic Values

 $(T_J = 25^\circ\text{C}, \text{unless otherwise specified})$

Symbol	Test Conditions	min.	typ.	max.
I_s	$V_{GS} = 0 \text{ V}$		80	A
I_{SM}	Repetitive; pulse width limited by T_{JM}		320	A
V_{SD}	$I_F = I_s, V_{GS} = 0 \text{ V}$, Pulse test, $t < 300 \text{ ms}$, duty cycle d < 2 %		1.3	V
t_{rr} Q_{RM} I_{RM}	$I_F = 30 \text{ A}, -di/dt = 100 \text{ A}/\mu\text{s}, V_R = 100 \text{ V}$	1.2 8	250 μC	ns A



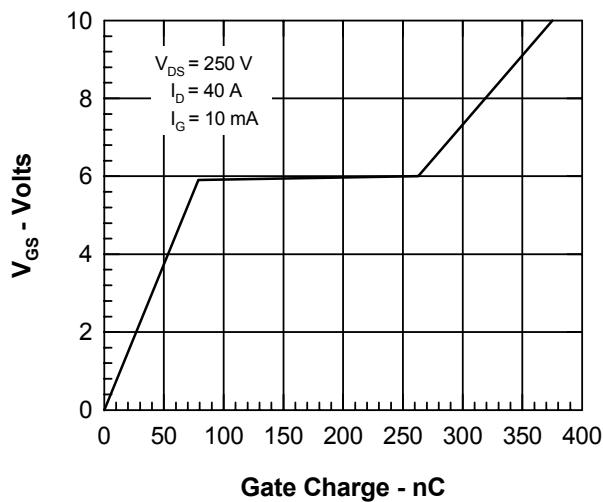


Fig. 7 Gate Charge Characteristic Curve

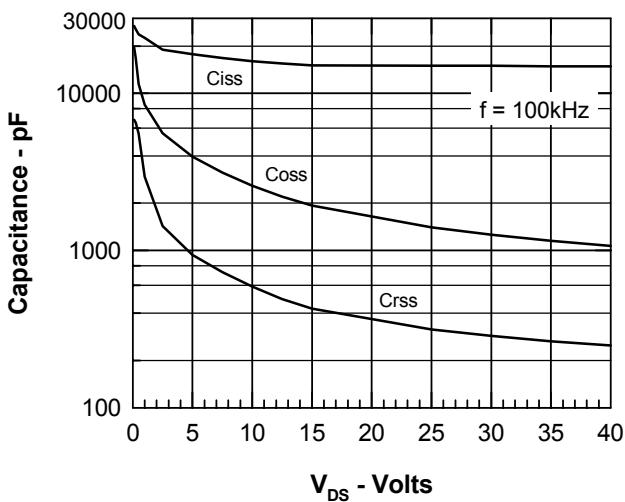


Fig. 8 Capacitance Curves

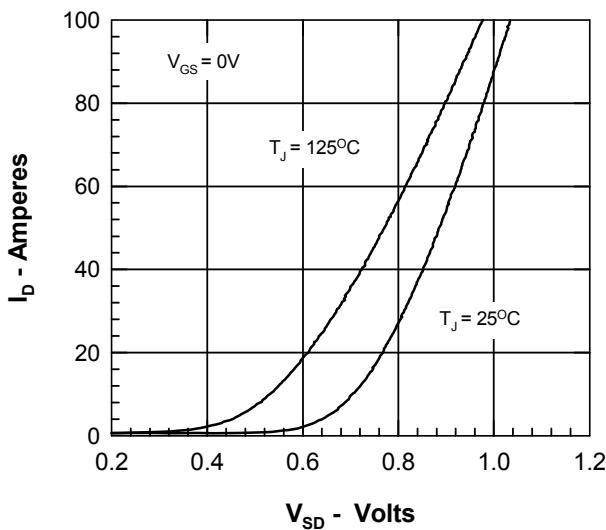


Fig. 9. Source-to-Drain Voltage Drop

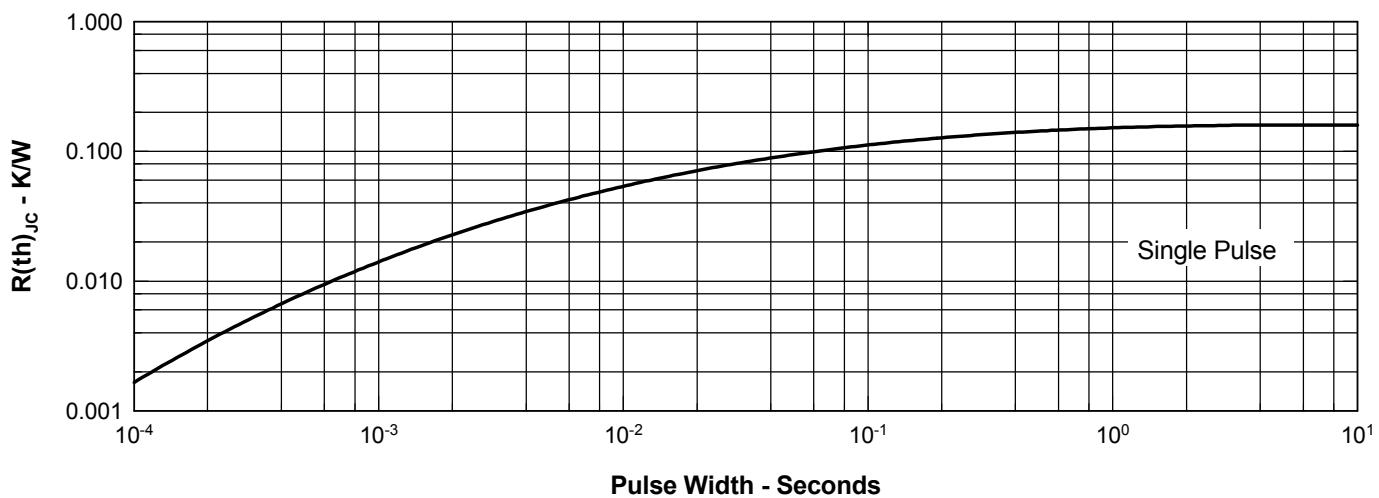


Fig. 10. Transient Thermal Resistance



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[25.163.2453.0](#) [25.163.4253.0](#) [25.190.2053.0](#) [25.194.3453.0](#) [25.320.4853.1](#) [25.320.5253.1](#) [25.326.3253.1](#) [25.326.3553.1](#) [25.330.1653.1](#)
[25.330.4753.1](#) [25.330.5253.1](#) [25.334.3253.1](#) [25.334.3353.1](#) [25.350.2053.0](#) [25.352.4753.1](#) [25.522.3253.0](#) [T483C](#) [T484C](#) [T485F](#) [T485H](#)
[T512F-YEB](#) [T513F](#) [T514F](#) [T554](#) [T612FSE](#) [25.161.3453.0](#) [25.179.2253.0](#) [25.194.3253.0](#) [25.325.1253.1](#) [25.326.4253.1](#) [25.330.0953.1](#)
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[25.640.5053.0](#)